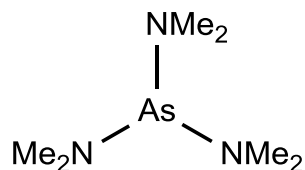


Catalog # 33-5000 Tris(dimethylamino)arsine, 99%



Technical Notes:

1. Precursor for arsenic doping in MOCVD of HgCdTe films. Absence of As–H bonds prevents the formation of As–H complexes and its incorporation in the As-doped films^[1]
2. ALD/CVD dopant for CdTe/CdS thin films for photovoltaics grown by MOCVD^[2-3]
3. ALD/CVD dopant for GaAs_(1-x)N_x films deposited by N-ALD technique^[4]
4. ALD/CVD precursor for *p*-type epitaxial growth of CdTe on *p*-type GaAs films^[5]
5. CVD precursor for GaAs thin films deposition from As(NMe₂)₃ and GaMe₃ for solar cells^[6]

References:

1. *J. Electron. Mater.*, **1996**, 25, 1328.
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6. *RSC Adv.*, **2015**, 5, 11812.